

GaAlAs-IR-Lumineszenzdiode (880 nm)

GaAlAs Infrared Emitter (880 nm)

SFH 485 P



Wesentliche Merkmale

- GaAlAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- Gute spektrale Anpassung an Si-Fotoempfänger
- Gegurtet lieferbar (im Ammo-Pack)
- Gruppiert lieferbar
- Gehäusegleich mit SFH 217

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Rauchmelder (UL-Freigabe)
- Sensorik
- Diskrete Lichtschranken

Features

- Very highly efficient GaAlAs-LED
- High reliability
- Spectral match with silicon photodetectors
- Available on tape and reel (in Ammopack)
- Available in bins
- Same package as SFH 217

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Smoke detectors (UL-approval)
- Sensor technology
- Discrete interrupters

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 485 P	Q62703-Q516	5-mm-LED-Gehäuse, plan, klares violettes Epoxy-Gießharz, Lötspieße im 2.54-mm-Raster ($1/10''$), Anodenkennzeichnung: kürzerer Anschluß 5 mm LED package (T 1 $3/4$), plane violet-colored transparent epoxy resin, solder tabs lead spacing 2.54 mm ($1/10''$), anode marking: short lead.

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlaßstrom Forward current	I_F	100	mA
Stoßstrom, $\tau \leq 10\text{ }\mu\text{s}$ Surge current	I_{FSM}	2.5	A
Verlustleistung Power dissipation	P_{tot}	200	mW
Wärmewiderstand, freie Beinchenlänge max. 10 mm Thermal resistance, lead length between package bottom and PC-board max. 10 mm	R_{thJA}	375	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$	λ_{peak}	880	nm
Spektrale Bandbreite bei 50% von I_{max} $I_F = 100\text{ mA}$ Spectral bandwidth at 50% of I_{max}	$\Delta\lambda$	80	nm
Abstrahlwinkel Half angle	φ	± 40	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm
Abstand Chipoberfläche bis Gehäusevorderseite Distance chip front to case surface	H	0.5 ... 1	mm

Kennwerte ($T_A = 25\text{ °C}$)
Characteristics (cont'd)

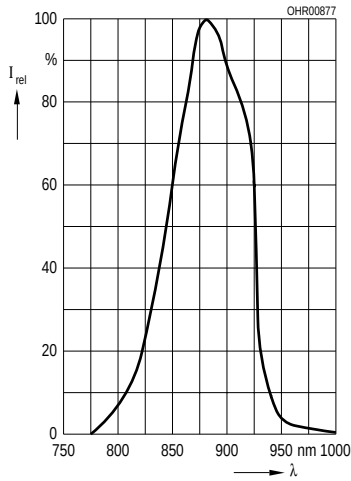
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 50\text{ mA}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$	t_r, t_f	0.6/0.5	μs
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$ Capacitance	C_o	15	pF
Durchlaßspannung, Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F	1.5 (< 1.8) 3.0 (< 3.8)	V
Sperrstrom, Reverse current $V_R = 5\text{ V}$	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluß, Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	25	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_{I_e}	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 2	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.25	nm/K

Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.01$ sr**Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.01$ sr

Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	I_e	> 3.15	mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ.}}$	48	mW/sr

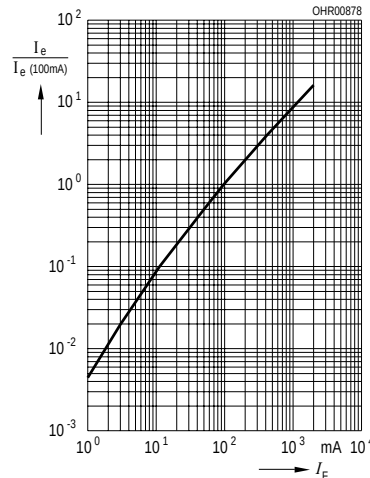
Relative Spectral Emission

$$I_{\text{rel}} = f(\lambda)$$



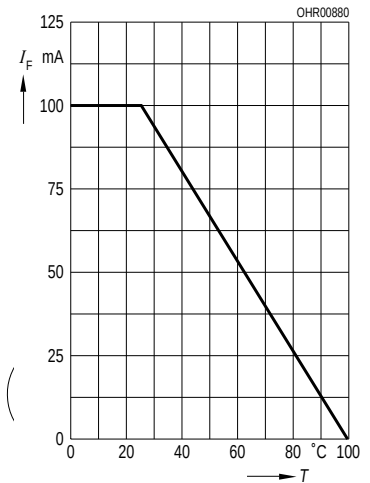
$$\text{Radiant Intensity } \frac{I_e}{I_e(100 \text{ mA})} = f(I_F)$$

Single pulse, $t_p = 20 \mu\text{s}$



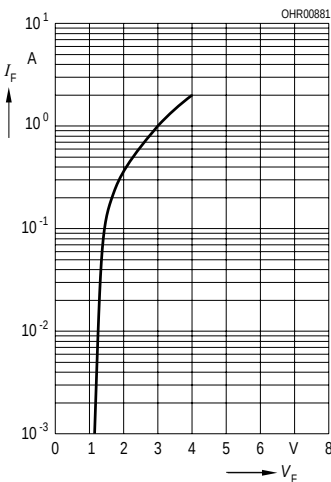
Max. Permissible Forward Current

$$I_F = f(T_A)$$



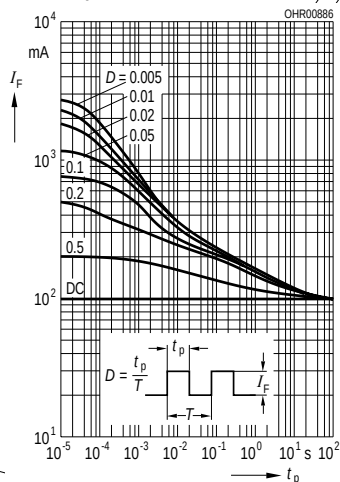
Forward Current

$$I_F = f(V_F), \text{ Single pulse, } t_p = 20 \mu\text{s}$$



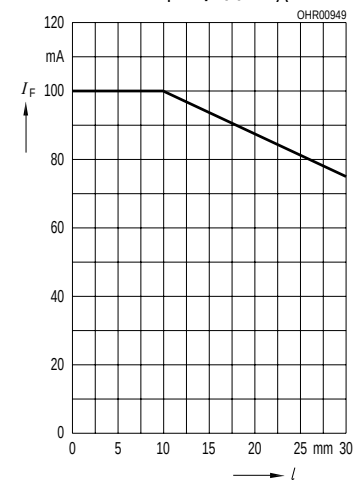
Permissible Pulse Handling Capability

$$I_F = f(\tau), T_A = 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$$



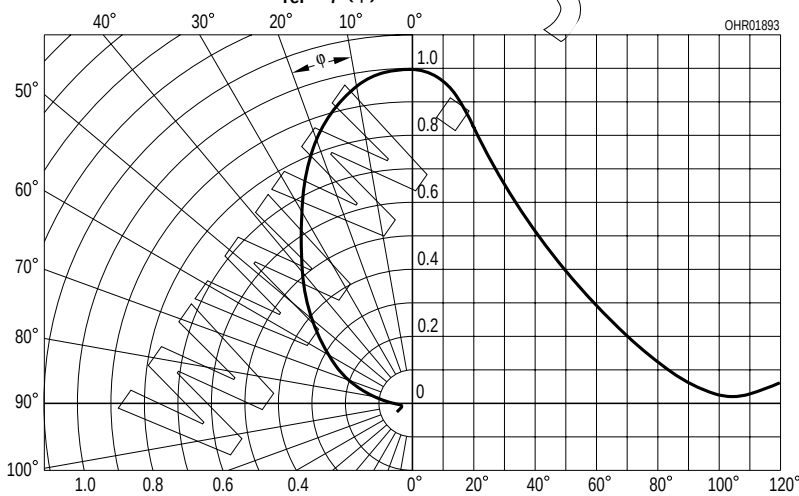
Forward Current vs. Lead Length Between the Package Bottom and the PC-Board

$$I_F = f(l), T_A = 25^\circ\text{C}$$

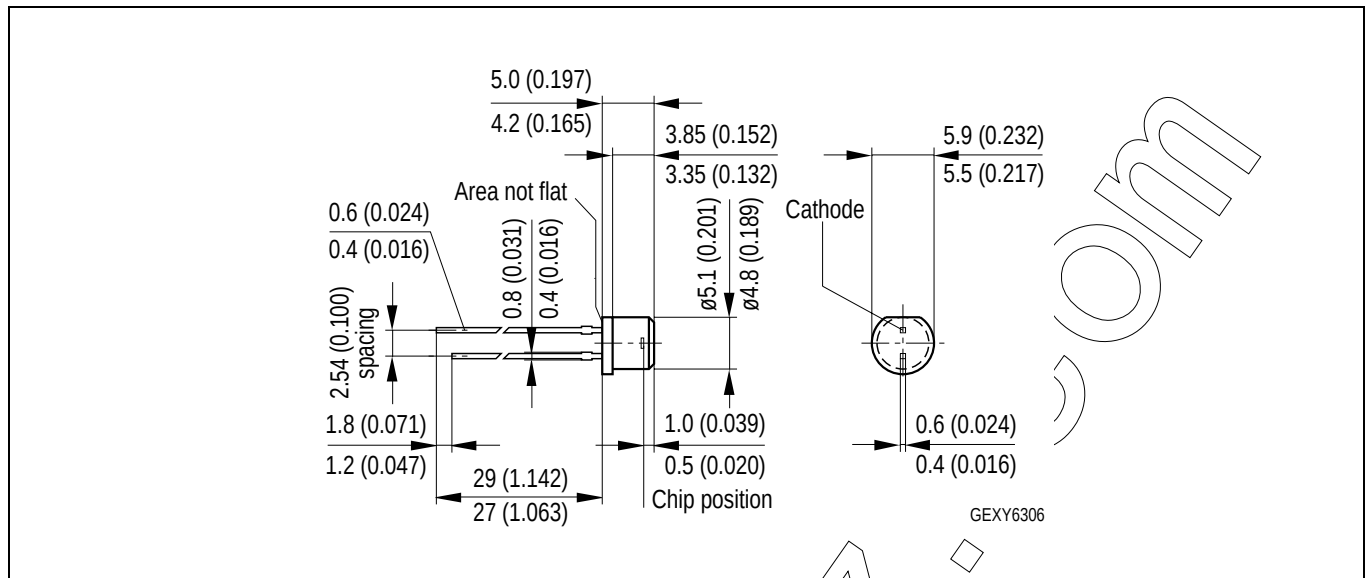


Radiation Characteristics

$$I_{\text{rel}} = f(\varphi)$$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Published by OSRAM Opto Semiconductors GmbH & Co. OHG
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